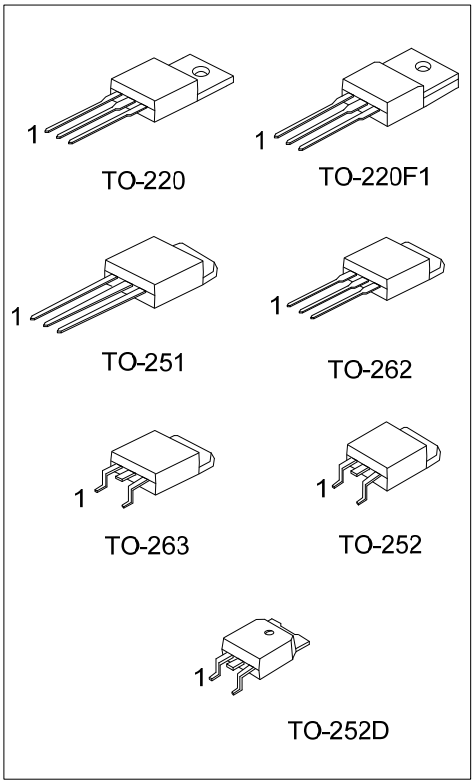
4N80-C

Power MOSFET

4.0A, 800V N-CHANNEL POWER MOSFET



■ DESCRIPTION

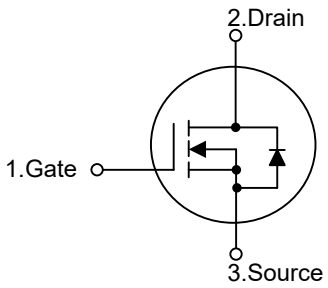
The UTC **4N80-C** is a N-channel mode power MOSFET using UTC's advanced technology to provide costomers planar stripe and DMOS technology. This technology is specialized in allowing a minimum on-state resistance, and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **4N80-C** is universally applied in high efficiency switch mode power supply.

■ FEATURES

* $R_{DS(on)} \leq 2.6\ \Omega$ @ V_{GS}=10V, I_D=2.0A
* High switching speed
* Improved dv/dt capability
* 100% avalanche tested

■ SYMBOL



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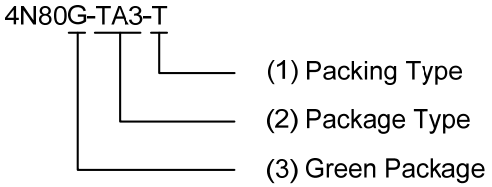
■ ORDERING INFORMATION

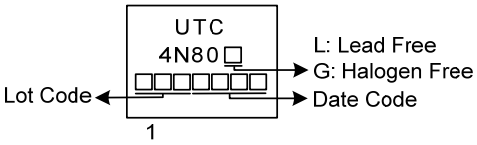
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
4N80L-TA3-T	4N80G-TA3-T	TO-220	G	D	S	Tube
4N80L-TF1-T	4N80G-TF1-T	TO-220F1	G	D	S	Tube
4N80L-TM3-T	4N80G-TM3-T	TO-251	G	D	S	Tube
4N80L-TN3-R	4N80G-TN3-R	TO-252	G	D	S	Tape Reel
4N80L-TND-R	4N80G-TND-R	TO-252D	G	D	S	Tape Reel
4N80L-T2Q-T	4N80G-T2Q-T	TO-262	G	D	S	Tube
4N80L-TQ2-T	4N80G-TQ2-T	TO-263	G	D	S	Tube
4N80L-TQ2-R	4N80G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF1: TO-220F1, TM3: TO-251, TN3: TO-252, TND: TO-252D, T2Q: TO-262, TQ2: TO-263
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	800	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	4	A
	Pulsed (Note 2)	I_{DM}	8	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	369	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.5	V/ns
Power Dissipation	TO-220/TO-262 TO-263	P_D	106	W
	TO-220F1		28	W
	TO-251/ TO-252 TO-252D		47	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L=57mH, I_{AS}=3.6A, V_{DD}= 50V, R_G=25Ω, Starting T_J=25°C
4. I_{SD} ≤4A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J=25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F1 TO-262/TO-263	θ_{JA}	62.5	°C/W
	TO-251/ TO-252 TO-252D		110	°C/W
Junction to Case	TO-220/TO-262 TO-263	θ_{JC}	1.18	°C/W
	TO-220F1		4.46	°C/W
	TO-251/ TO-252 TO-252D		2.65 (Note)	°C/W

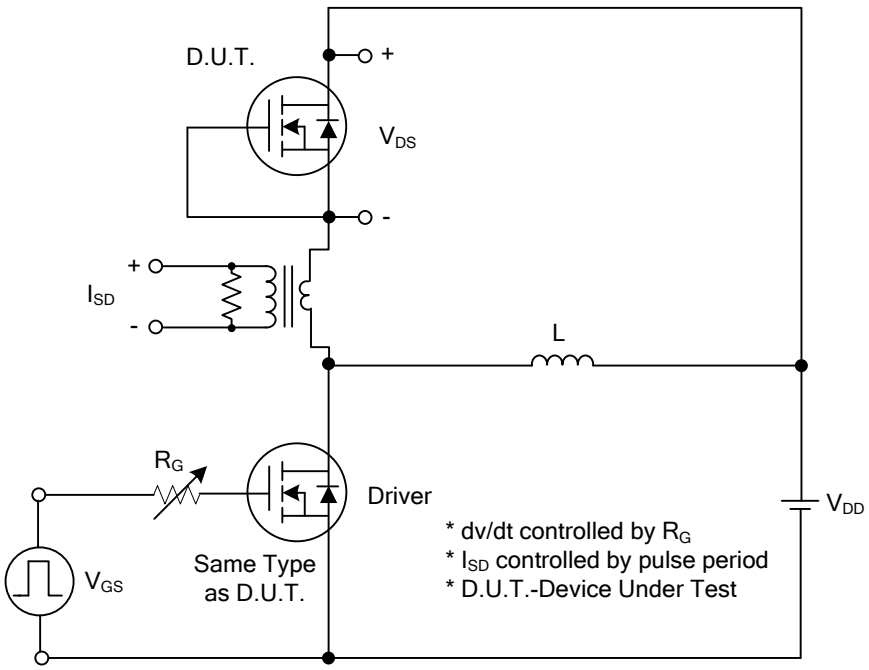
Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

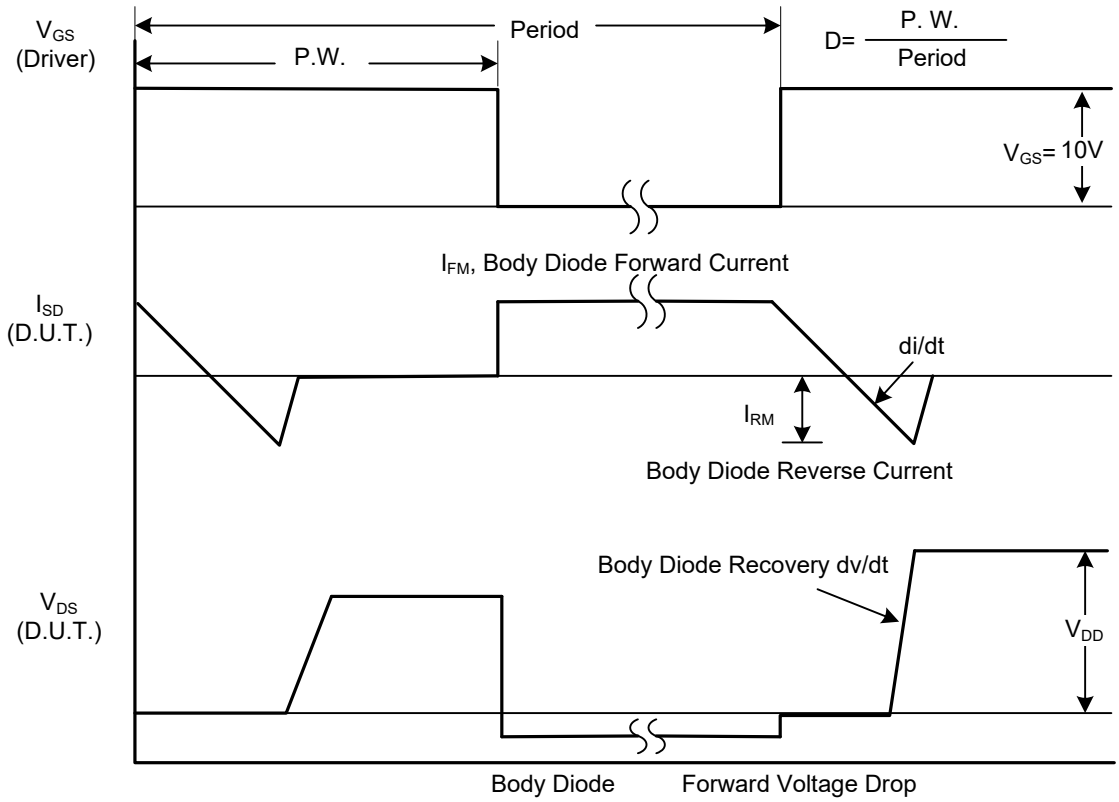
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	800			V
Breakdown Voltage Temperature Coefficient		$\Delta BV_{DSS}/\Delta T_J$	I_D=250μA,Referenced to 25°C		900		mV/°C
Drain-Source Leakage Current		I_{DSS}	V_{DS}=800V, V_{GS}=0V			10	μA
			V_{DS}=640V, T_C=125°C			100	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{DS}=0V ,V_{GS}=30V			100	nA
	Reverse		V_{DS}=0V ,V_{GS}=-30V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	3.0		5.0	V
Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=2.0A			2.6	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V,V_{DS}=25V, f=1.0MHz		870		pF
Output Capacitance		C_{OSS}			105		pF
Reverse Transfer Capacitance		C_{RSS}			12		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=640V, V_{GS}=10V, I_D=4.0A (Note 1,2)		32		nC
Gate-Source Charge		Q_{GS}			12		nC
Gate-Drain Charge		Q_{GD}			9		nC
Turn-ON Delay Time (Note 1)		$t_{D(ON)}$	V_{DD}=400V, I_D=4.0A, R_G=25Ω (Note 1,2)		16		ns
Turn-ON Rise Time		t_R			20		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			70		ns
Turn-OFF Fall Time		t_F			34		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				4	A
Maximum Body-Diode Pulsed Current		I_{SM}				8	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	I_S =4.0A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t_{rr}	I_S =4.0A, V_{GS}=0V, dI_F/dt=100A/μs (Note 1)		520		ns
Body Diode Reverse Recovery Charge		Q_{rr}			4.3		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

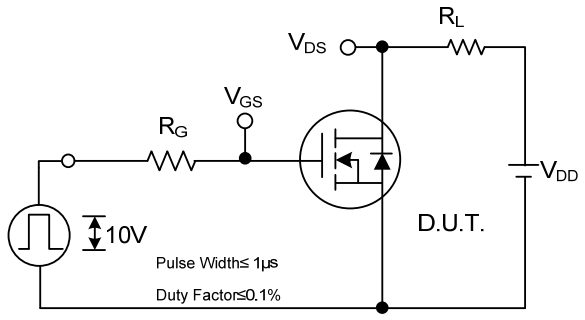


Peak Diode Recovery dv/dt Test Circuit

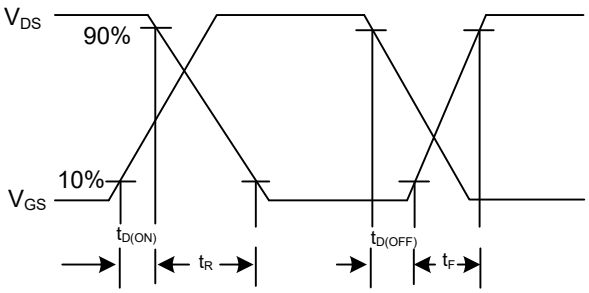


Peak Diode Recovery dv/dt Waveforms

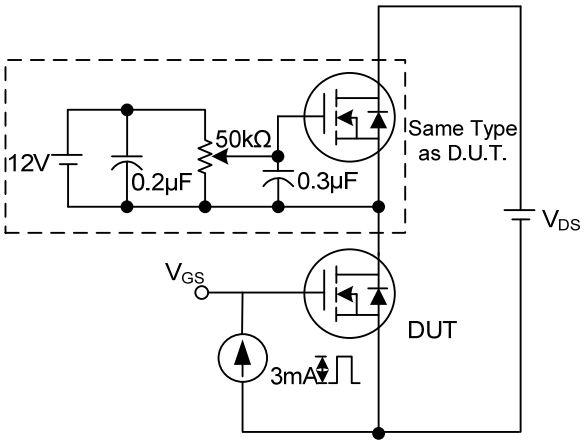
■ TEST CIRCUITS AND WAVEFORMS



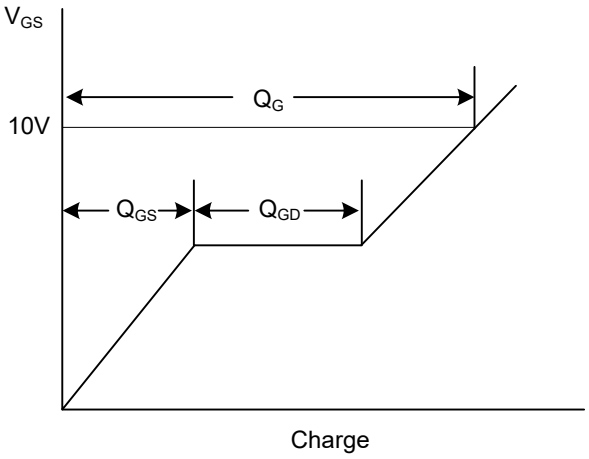
Switching Test Circuit



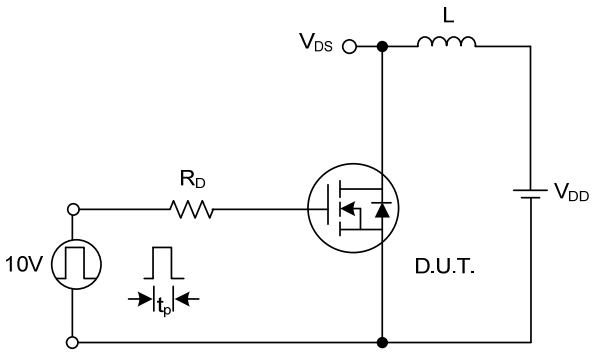
Switching Waveforms



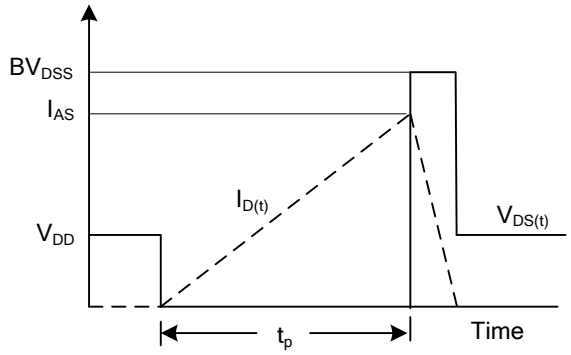
Gate Charge Test Circuit



Gate Charge Waveform



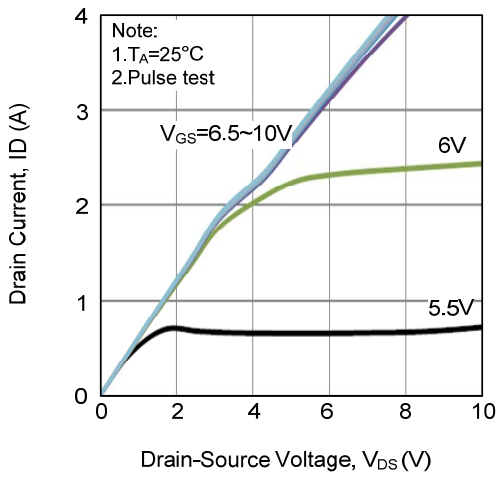
Unclamped Inductive Switching Test Circuit



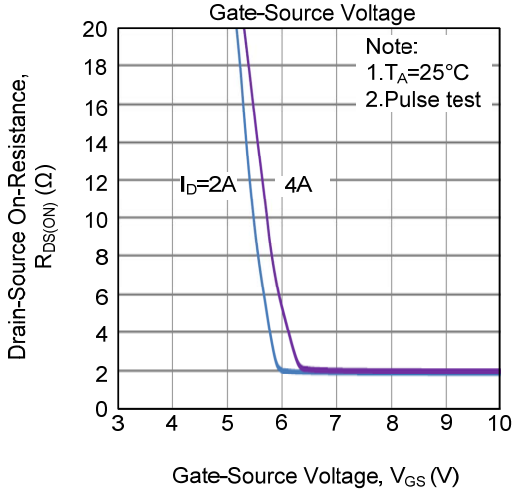
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

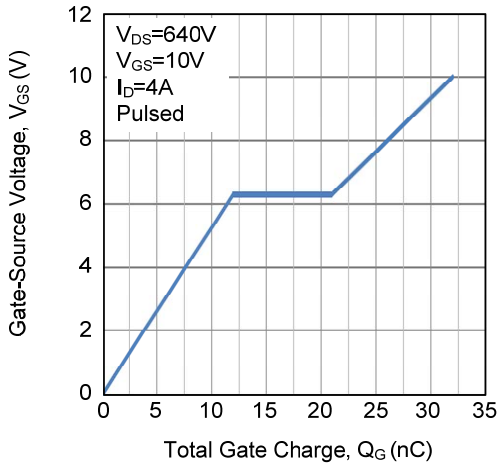
Drain Current vs. Drain-Source Voltage



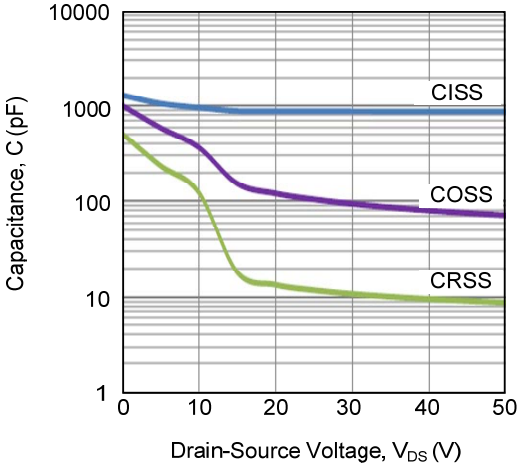
Drain-Source On-Resistance vs. Gate-Source Voltage



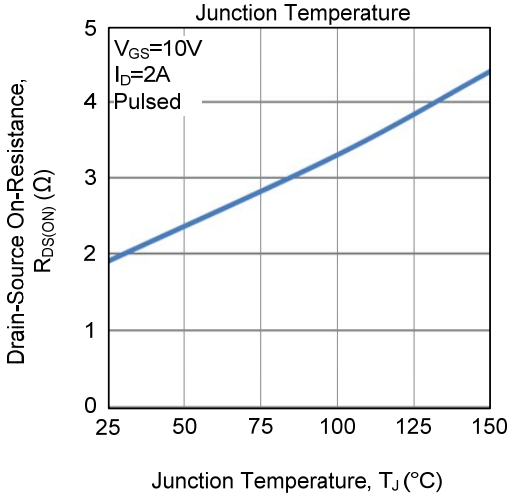
Gate Charge Characteristics



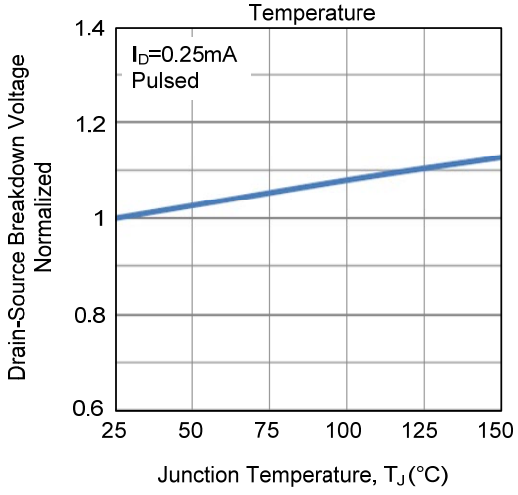
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

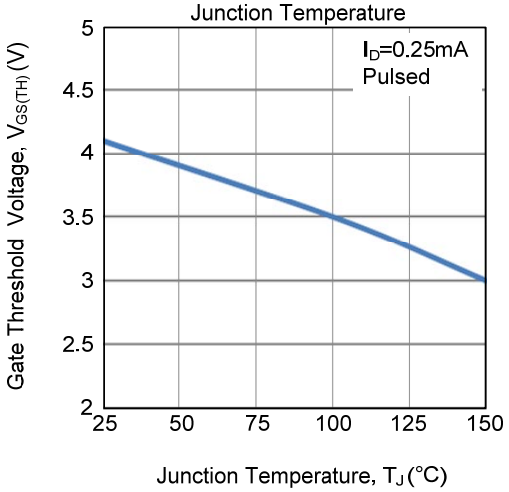


Breakdown Voltage vs. Junction Temperature

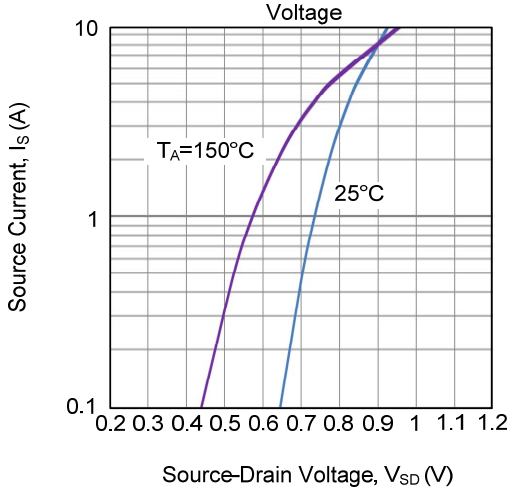


■ TYPICAL CHARACTERISTICS (Cont.)

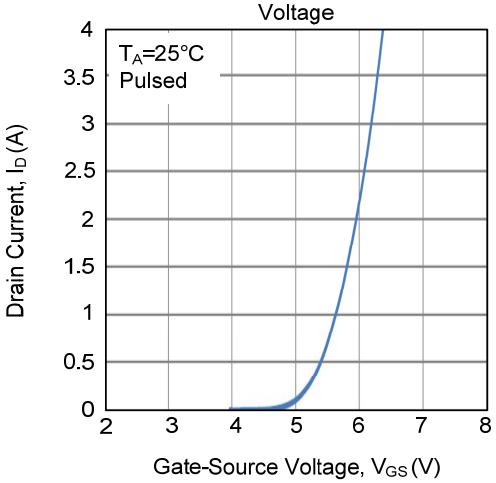
Gate Threshold Voltage vs. Junction Temperature



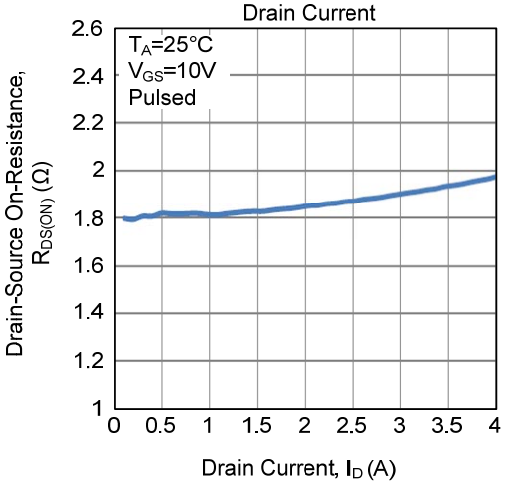
Source Current vs. Source-Drain Voltage



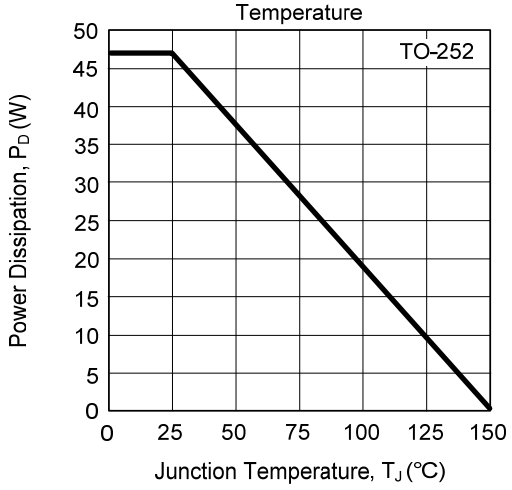
Drain Current vs. Gate-Source Voltage



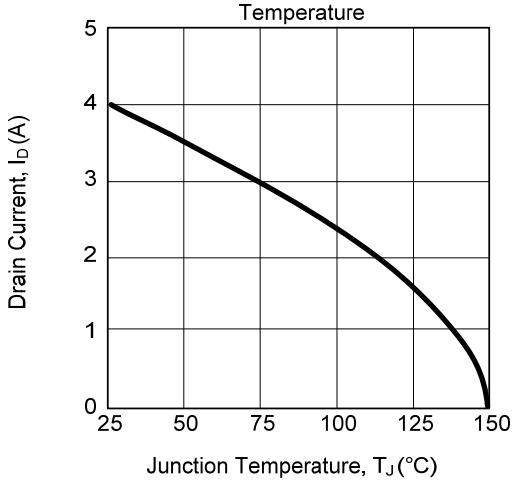
Drain-Source On-Resistance vs. Drain Current



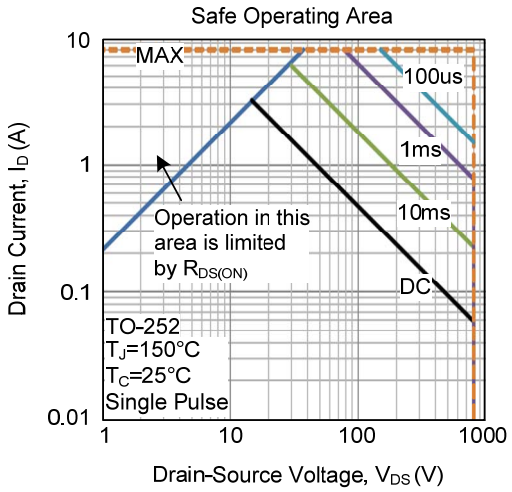
Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)



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